

Customer No.: 31561  
Application No: 10/605,458  
Docket No.:9776-US-PA

### Claim Amendment

Please amend the claims according to the following listing of claims and substitute it for all prior versions and listings of claims in the application.

1. (currently amended) A pixel structure on a transparent substrate, the pixel structure comprising:

a scan line over the transparent substrate;

a gate insulation layer over the transparent substrate covering the scan line;

a data line over the gate insulation layer, wherein the data line extends in a direction perpendicular to the direction of extension of the scan line;

a pair of shelling layers with each shelling layer over the transparent substrate positioned on each side of the data line, wherein the shelling layers on each side of the data line are electrically connected;

a thin film transistor over the transparent substrate, wherein the thin film transistor has a gate electrode, a channel layer and a pair of source/drain terminals, the source terminal is electrically connected to the data line, the gate electrode is electrically connected to the scan line and the channel layer is formed over the gate insulation layer above the gate electrode;

a passivation layer over the transparent substrate covering the thin film transistor and the data line;

a contact within the passivation layer; and

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a pixel electrode over the passivation layer, wherein the pixel electrode is electrically connected to the drain terminal through the contact.

2. (currently amended) The pixel structure of claim 1, wherein ~~the~~ each shelling layer further includes:

a shelling section over the transparent substrate on each side of the data line;

and

a connective section over the transparent substrate, wherein the connective section joins up the shelling section on each side of the data line electrically.

3. (original) The pixel structure of claim 1, wherein the shelling layer includes a block of shelling metallic layer that crosses from one side of the data line to the other.

4. (original) The pixel structure of claim 1, wherein the shelling layer, the gate electrode and the scan line are all fabricated using an identical material.

5. (currently amended) A pixel structure on a transparent substrate, the pixel structure comprising:

a scan line over the transparent substrate;

a gate insulation layer over the transparent substrate covering the scan line;

a data line over the gate insulation layer, wherein the data line extends in a direction perpendicular to the direction of extension of the scan line;

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a pair of shelling layers over the transparent substrate respectively on each side of the data line, wherein the shelling layers on each side of the data line are electrically connected;

a dielectric layer between the data line and the gate insulation layer above the shelling layer;

a thin film transistor over the transparent substrate, wherein the thin film transistor has a gate electrode, a channel layer and a pair of source/drain terminals, wherein the source terminal is electrically connected to the data line, the gate electrode is electrically connected to the scan line and the channel layer is formed over the gate insulation layer above the gate electrode;

a passivation layer over the transparent substrate covering the thin film transistor and the data line;

a contact within the passivation layer; and

a pixel electrode over the transparent substrate, wherein the pixel electrode and the drain terminal are electrically connected through the contact.

6. (original) The pixel structure of claim 5, wherein the dielectric layer includes a silicon nitride layer.

7. (cancelled)

8. (original) The pixel structure of claim ~~7~~5, wherein ~~the~~ each shelling layer further includes:

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a shelling section over the transparent substrate on each side of the data line;  
and

a connective section over the transparent substrate, wherein the connective section joins up the shelling sections on ~~each~~ both sides of the data line electrically.

9. (original) The pixel structure of claim 8, wherein the shelling layer includes a block of shelling metallic layer that crosses from one side of the data line to the other.

10. (original) The pixel structure of claim 5, wherein the shelling layer, the gate electrode and the scan line are all fabricated using an identical material.

11. (currently amended) A method of forming a pixel structure, comprising the steps of:  
forming a gate electrode and a scan line having a connection with the gate electrode over a transparent substrate and forming a pair of shelling layers over the transparent substrate at the same time, wherein ~~the~~ each shelling layer is formed on each side of an area destined to form a data line and the shelling layers on each side are electrically connected together;

forming a gate insulation layer over the transparent substrate covering the gate electrode, the scan line and the shelling layer;

forming a channel layer over the gate insulation layer above the gate electrode;

forming a pair of source/drain terminals over the channel layer and forming a data line having connection with the source terminal over the gate insulation layer at the same

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time, wherein the gate electrode, the channel layer and the source/drain terminals together constitute a thin film transistor;

forming a passivation layer over the transparent substrate covering the thin film transistor and the data line;

forming an opening that exposes the drain terminal in the passivation layer; and

forming a pixel electrode over the passivation layer, wherein the pixel electrode and the drain terminal are electrically connected through a contact in the opening.

12. (currently amended) The method of claim 11, wherein ~~the each~~ shelling layer includes a shelling section on each side of the data line and a connective section joining the shelling sections electrically.

13. (original) The method of claim 11, wherein the shelling layer is a block of shelling metallic layer that crosses from one side of the data line to the other side.

14. (original) The method of claim 11, wherein the shelling layer, the gate electrode and the scan line are all fabricated using an identical material.

15. (currently amended) A method of forming a pixel structure, comprising the steps of:  
forming a gate electrode and a scan line having a connection with the gate electrode over a transparent substrate and forming a shelling layer over the transparent substrate at the same time, wherein the shelling layer is formed on each side of an area destined to form a data line and the shelling layers on each side are electrically connected together;

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forming a gate insulation layer over the transparent substrate covering the gate electrode, the scan line and the shelling layer;

forming a channel layer over the gate insulation layer above the gate electrode;

forming a dielectric layer over the gate insulation layer above the shelling layer;

forming a pair of source/drain terminals over the channel layer and forming a data line having connection with the source terminal over the gate insulation layer at the same time, wherein the gate electrode, the channel layer and the source/drain terminals together constitute a thin film transistor;

forming a passivation layer over the transparent substrate covering the thin film transistor and the data line;

forming an opening that exposes the drain terminal in the passivation layer; and

forming a pixel electrode over the passivation layer, wherein the pixel electrode and the drain terminal are electrically connected through a contact in the opening.

16. (original) The method of claim 15, wherein the dielectric layer is a silicon nitride layer.

17. (original) The method of claim 15, wherein the shelling layers on each side of the data line are electrically connected together.

18. (original) The method of claim 17, wherein the shelling layer includes a shelling sections on each side of the data line and a connective section joining the shelling sections electrically.

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19. (original) The method of claim 17, wherein the shelling layer is a block of shelling metallic layer that crosses from one side of the data line to the other side.

20. (original) The method of claim 15, wherein the shelling layer, the gate electrode and the scan line are all fabricated using an identical material.

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